

**AMENDMENT TO THE CLAIMS**

A copy of all pending claims and a status of the claims is provided below.

Claims 1-16 (Canceled)

Claim 17 (Original) A semiconductor structure, comprising:

a channel having a fin of strained Si vertically oriented on a non-conductive substrate.

Claim 18 (Original) The structure of Claim 17, wherein the strained Si film is between about 50 Å and 200 Å thick.

Claim 19 (Original) The structure of Claim 17, wherein the strained Si film is epitaxially grown on a block of relaxed SiGe, wherein the relaxed SiGe comprises a range of Ge ranging from about 0% to 100%.

Claim 20 (Original) The structure of Claim 17, further comprising a gate comprising at least one of an oxide and a high k material formed on a first side of the strained Si film.

Claim 21 (Original) The structure of Claim 20, further comprising a gate comprising at least one of an oxide and a high k material formed on a top and a second side of the strained Si film.

Claim 22 (Original) The structure of claim 20, wherein the Si film is a low defect strained Si film.